

### **Dual NPN Small Signal Surface Mount Transistor**

### **Description**

The MMDT2222A is a Dual NPN Small Signal Surface Mount Transistor, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The SOT-363 package which has been designed to achieve very low on-state resistance providing also one of the best-in-class figure of merit (FOM)

#### **Features**

- · Epitaxial planar die construction.
- · Complementary PNP type available MMBT2907A.
- · Ultra-small surface mount package.
- RoHS compliant package

#### **Application**

· Dual NPN small signal surface mount transistor

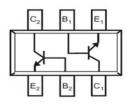
### **Packing & Order Information**

3,000/Reel

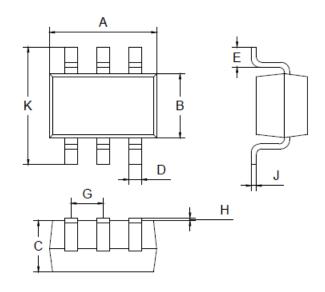


RoHS COMPLIANT

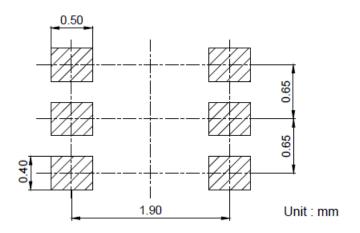
### **Graphic symbol**



SOT-363



### SOLDERING FOOTPRINT



### Dimensions in mm

SOT-363				
Dim	Min	Max		
Α	2.00	2.20		
В	1.15	1.35		
С	0.95 Typical			
D	0.25 Typical			
Е	0.25	0.40		
G	0.60	0.70		
Н	0.02	0.10		
J	0.10 Typical			
K	2.2	2.4		
All Dimensions in mm				



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATING @ Ta=25°C unless otherwise specified				
Symbol	Parameter	Value	Unit	
$V_{CBO}$	Collector-Base Voltage	75	V	
$V_{CEO}$	Collector-Emitter Voltage	40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	A	
I <sub>C</sub>	Collector Current -Continuous	600	mA	
P <sub>D</sub>	Collector Dissipation	200	mW	
$R_{\theta JA}$	Thermal resistance junction to ambient	625	°C/W	
Tj,Tstg	Junction and Storage Temperature	-55 to +150	°C	

Symbol	Parameter	Test Conditions	MIN	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_{C} = 10\mu A$ , $I_{E} = 0$	75		V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = 10mA , I <sub>B</sub> = 0	40		V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	$I_E = 10\mu A$ , $I_C = 0$	6		V
I <sub>CBO</sub>	Collector cut-off current	$V_{CB} = 60 \text{ V}, I_{E} = 0$ $V_{CB} = 60 \text{ V}, I_{E} = 0, T_{A} = 150^{\circ}\text{C}$		10	nΑ μΑ
I <sub>CBX</sub>	Collector cut-off current	$V_{CE}$ = 60 V , $V_{EB(off)}$ = 3.0 V		10	nA
I <sub>EBO</sub>	Emitter cut-off current	$V_{EB} = 3 V$ , $I_C = 0$		10	nA
I <sub>BL</sub>	Base Cut-off Current	V <sub>CE</sub> = 60 V , V <sub>EB(off)</sub> = 3.0 V		20	nA
h <sub>FE</sub> DC current gain	DC current gain	$V_{CE} = 10 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	35 50 75 100	300	_
	DO current gain	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}, T_{A} = 55^{\circ}\text{C}$ $V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}$	40 50 35	300	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 500 \text{mA}$ , $I_B = 50 \text{mA}$ $I_C = 150 \text{mA}$ , $I_B = 15 \text{mA}$		1.0 0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I <sub>C</sub> = 500mA , I <sub>B</sub> = 50mA I <sub>C</sub> = 150mA , I <sub>B</sub> = 15mA	0.6	2.0 1.2	V
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> = 20 V , I <sub>C</sub> = 20mA , f = 100MHz	300		MHz

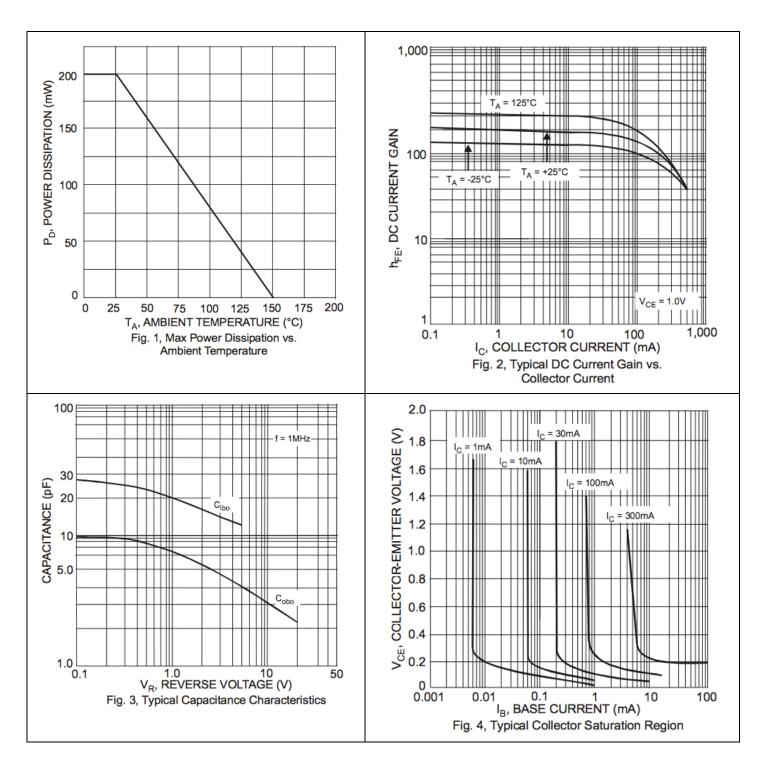


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ELECTRIC	ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified					
Symbol	Parameter	Test Conditions	MIN	MAX	UNIT	
C <sub>obo</sub>	Output capacitance	$V_{CB} = 10 \text{ V}$ , $I_E = 0$ , $f = 1.0 \text{MHz}$		8	pF	
$C_{ibo}$	Input capacitance	$V_{EB} = 0.5 V$ , $I_C = 0$ , $f = 1.0 MHz$		25	pF	
NF	Noise Figure	$V_{CE} = 10 \text{ V}, f = 1.0 \text{kHz},$ $I_{C} = 100 \mu\text{A}, R_{S} = 1.0 \text{k}\Omega$		4	dB	
t <sub>d</sub>	Delay time	Vcc = 30 V, V <sub>BE(off)</sub> = -0.5 V		10	ns	
t <sub>r</sub>	Rise time	I <sub>C</sub> = 150mA , I <sub>B1</sub> = 15mA		25	ns	
t <sub>s</sub>	Storage time	V <sub>CC</sub> = 30 V, I <sub>C</sub> = 150mA		225	ns	
t <sub>f</sub>	Fall time	$I_{B1} = -I_{B2} = 15mA$		60	ns	

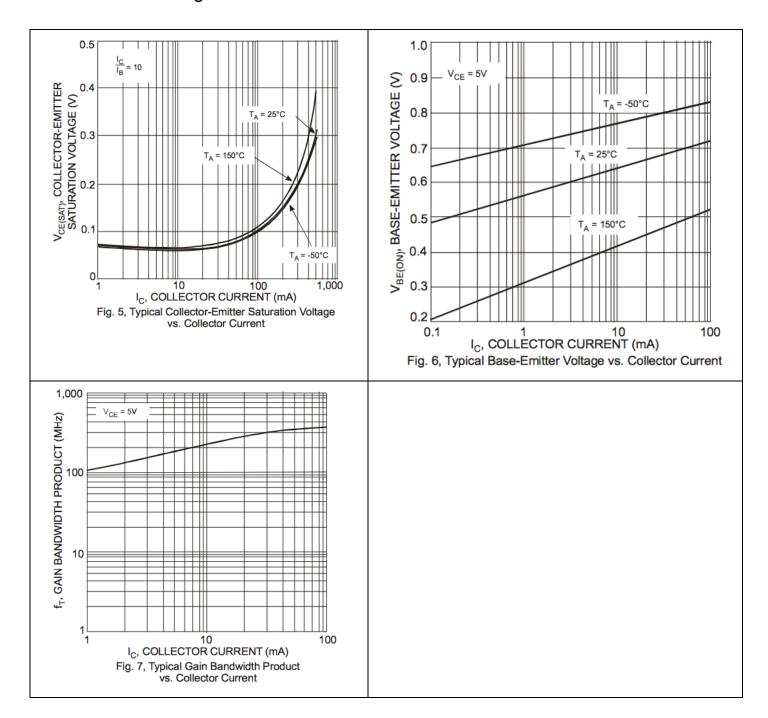


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